

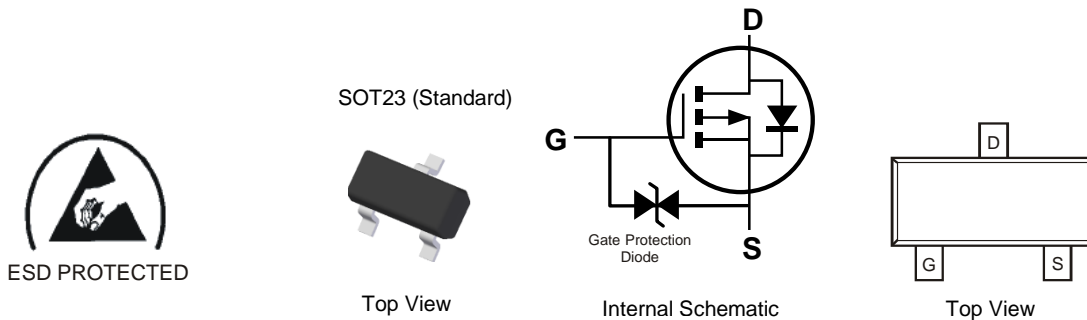
## Features

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **The DMP2035UQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.**

<https://www.diodes.com/quality/product-definitions/>

## Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 ③
- Terminal Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)

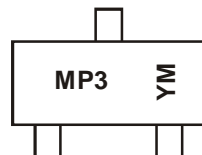


## Ordering Information (Notes 4 & 5)

Part Number	Compliance	Case	Packaging
DMP2035U-7	Standard	SOT23 (Standard)	3,000 / 7" Tape & Reel
DMP2035UQ-7	Automotive	SOT23 (Standard)	3,000 / 7" Tape & Reel
DMP2035U-13	Standard	SOT23 (Standard)	10,000 / 13" Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
  2. See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
  3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
  4. For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.
  5. The ESD gate protection diode is only designed to protect against ESD events. No gate-source voltage greater than the maximum  $V_{GSS}$  rating (given on page 2) can be applied.

## Marking Information



MP3 = Product Type Marking Code  
 YM = Date Code Marking  
 Y or  $\bar{Y}$  = Year (ex: I = 2021)  
 M = Month (ex: 9 = September)

### Date Code Key

Year	2011	...	2021	2022	2023	2024	2025	2026	2027	2028	2029	2030
Code	Y	...	I	J	K	L	M	N	O	P	R	S

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

**Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V <sub>DSS</sub>	-20	V	
Gate-Source Voltage	V <sub>GSS</sub>	±10	V	
Continuous Drain Current (Note 8) V <sub>GS</sub> = -4.5V	I <sub>D</sub>	T <sub>A</sub> = +25°C	-4.9	A
		T <sub>A</sub> = +70°C	-4.0	
Pulsed Drain Current (Note 8)	I <sub>DM</sub>	-24	A	
Maximum Continuous Body Diode Forward Current (Note 7)	I <sub>S</sub>	-1.2	A	
Pulsed Body Diode Forward Current (Note 10)	I <sub>SM</sub>	-24	A	

**Thermal Characteristics**

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 6)	P <sub>D</sub>	0.81	W
Thermal Resistance, Junction to Ambient (Note 6)	R <sub>θJA</sub>	153.5	°C/W
Total Power Dissipation (Note 7)	P <sub>D</sub>	1.2	W
Thermal Resistance, Junction to Ambient (Note 7)	R <sub>θJA</sub>	100	°C/W
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
<b>OFF CHARACTERISTICS (Note 9)</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C	I <sub>DSS</sub>	—	—	-1.0	μA	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V
Gate-Source Leakage	I <sub>GSS</sub>	—	—	±10	μA	V <sub>GS</sub> = ±8V, V <sub>DS</sub> = 0V
<b>ON CHARACTERISTICS (Note 9)</b>						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.4	-0.7	-1.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	—	23	35	mΩ	V <sub>GS</sub> = -4.5V, I <sub>D</sub> = -4.0A
			30	45		V <sub>GS</sub> = -2.5V, I <sub>D</sub> = -4.0A
			41	62		V <sub>GS</sub> = -1.8V, I <sub>D</sub> = -2.0A
Forward Transfer Admittance	Y <sub>FS</sub>	—	14	—	s	V <sub>DS</sub> = -5V, I <sub>D</sub> = -4A
Diode Forward Voltage	V <sub>SD</sub>	—	-0.7	-1.0	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1A
<b>DYNAMIC CHARACTERISTICS (Note 10)</b>						
Input Capacitance	C <sub>iss</sub>	—	1,610	—	pF	V <sub>DS</sub> = -10V, V <sub>GS</sub> = 0V f = 1.0MHz
Output Capacitance	C <sub>oss</sub>	—	157	—	pF	
Reverse Transfer Capacitance	C <sub>rss</sub>	—	145	—	pF	
Gate Resistance	R <sub>g</sub>	—	9.45	—	Ω	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 0V, f = 1MHz
Total Gate Charge	Q <sub>g</sub>	—	15.4	—	nC	V <sub>GS</sub> = -4.5V, V <sub>DS</sub> = -10V, I <sub>D</sub> = -4A
Gate-Source Charge	Q <sub>gs</sub>	—	2.5	—	nC	
Gate-Drain Charge	Q <sub>gd</sub>	—	3.3	—	nC	
Turn-On Delay Time	t <sub>D(ON)</sub>	—	16.8	—	ns	V <sub>DS</sub> = -10V, V <sub>GS</sub> = -4.5V, R <sub>L</sub> = 10Ω, R <sub>g</sub> = 6.0Ω, I <sub>D</sub> = -1A
Turn-On Rise Time	t <sub>R</sub>	—	12.4	—	ns	
Turn-Off Delay Time	t <sub>D(OFF)</sub>	—	94.1	—	ns	
Turn-Off Fall Time	t <sub>F</sub>	—	42.4	—	ns	

- Notes:
6. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
  7. Device mounted on FR-4 substrate PC board, 2oz copper, with 25mm X 25mm square copper plate.
  8. Repetitive rating, pulse width limited by junction temperature.
  9. Short duration pulse test used to minimize self-heating effect.
  10. Guaranteed by design. Not subject to product testing.

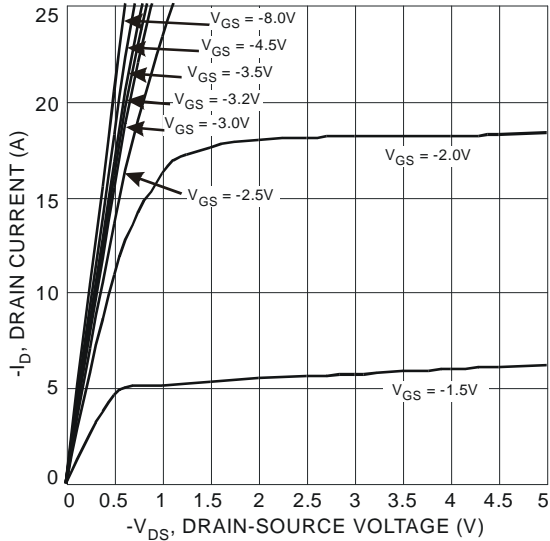


Fig. 1 Typical Output Characteristic

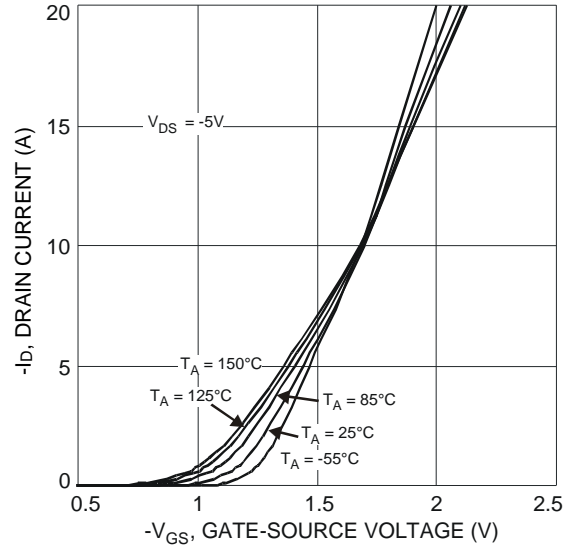


Fig. 2 Typical Transfer Characteristic

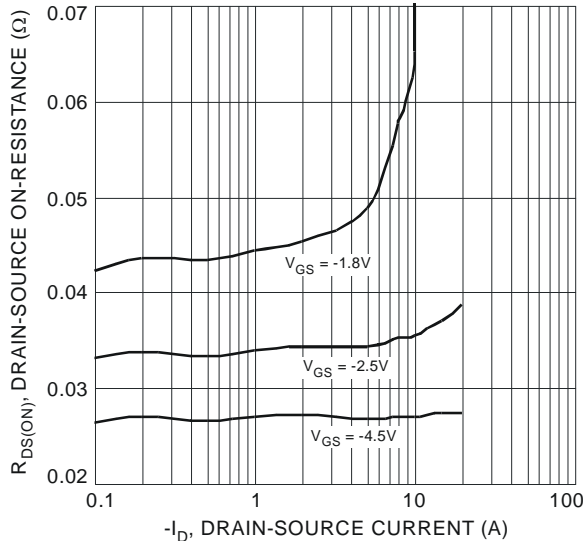


Fig. 3 Typical On-Resistance vs. Drain Current and Gate Voltage

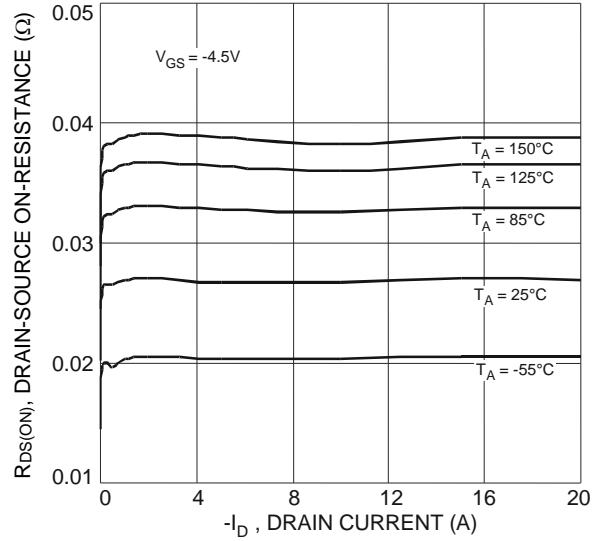


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

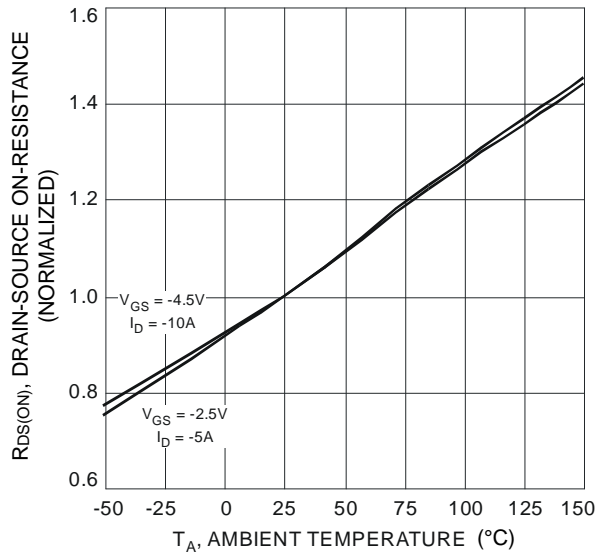


Fig. 5 On-Resistance Variation with Temperature

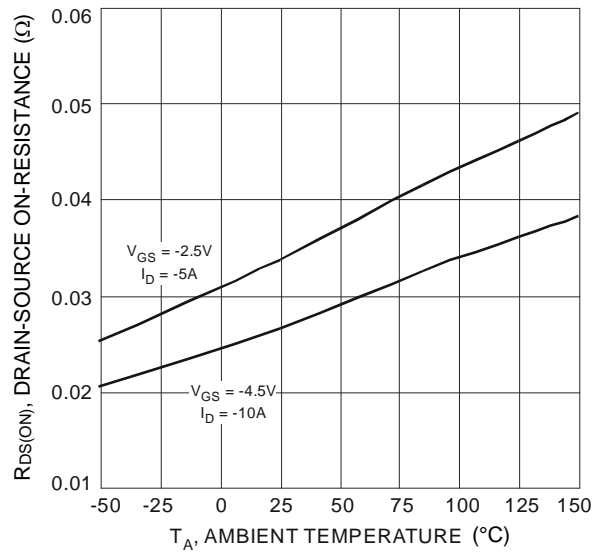


Fig. 6 On-Resistance Variation with Temperature

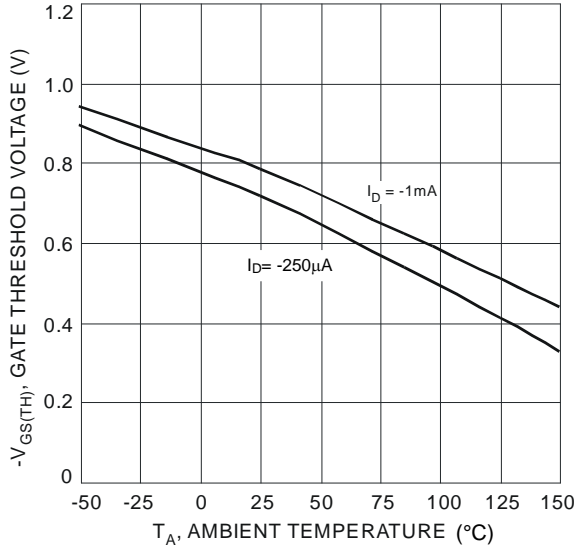


Fig. 7 Gate Threshold Variation vs. Ambient Temperature

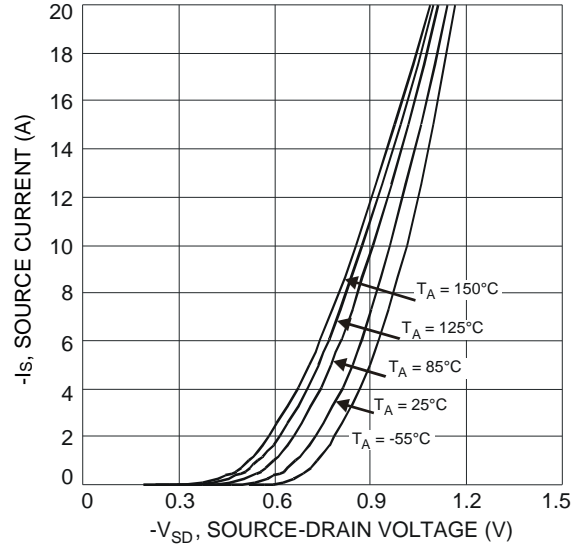


Fig. 8 Diode Forward Voltage vs. Current

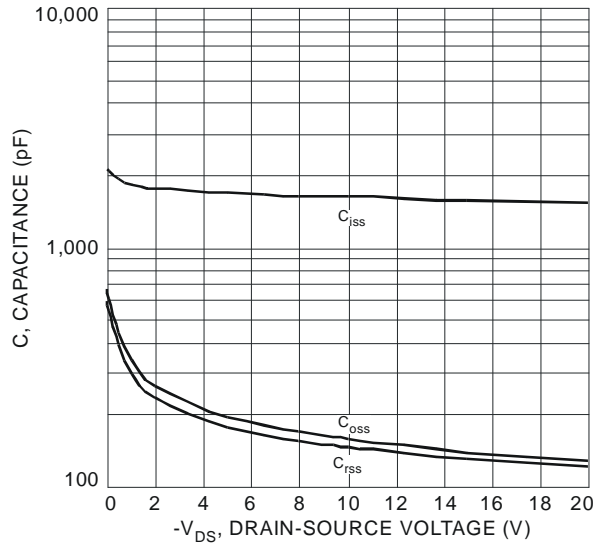


Fig. 9 Typical Total Capacitance

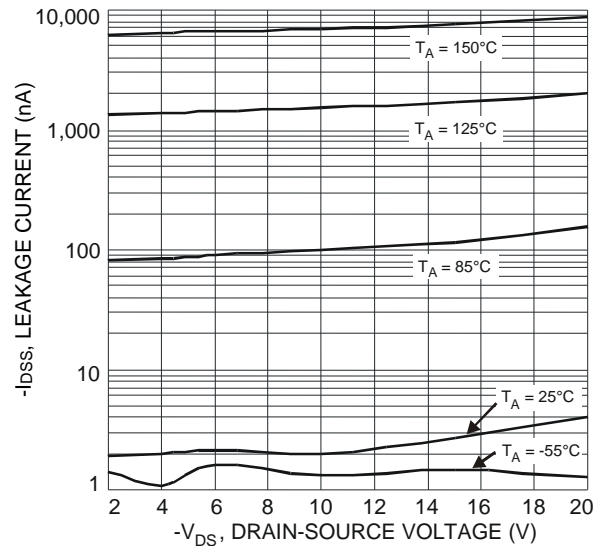


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

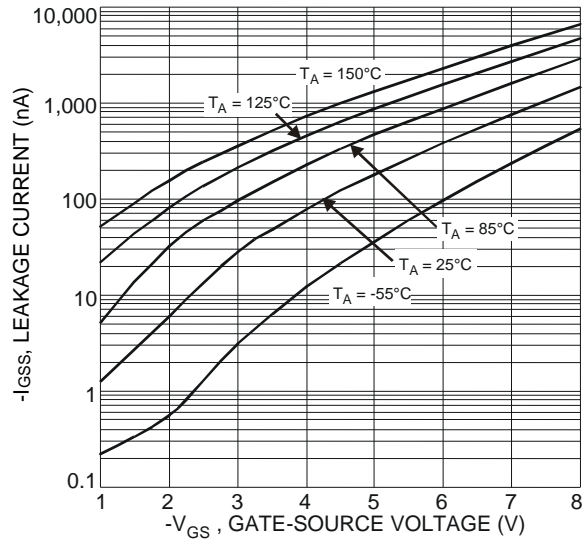


Fig. 11 Gate-Source Leakage Current vs. Voltage

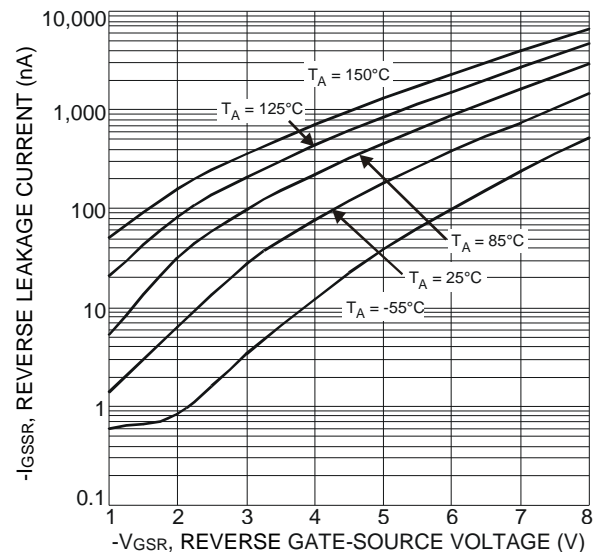


Fig. 12 Reverse Gate-Source Leakage Current vs. Voltage

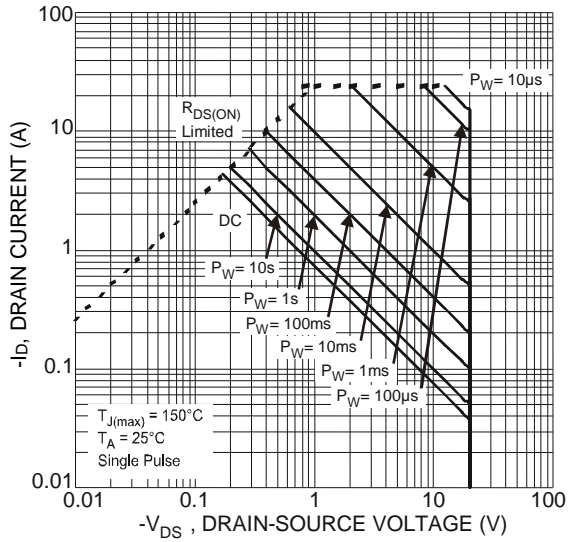


Fig. 13 SOA, Safe Operation Area

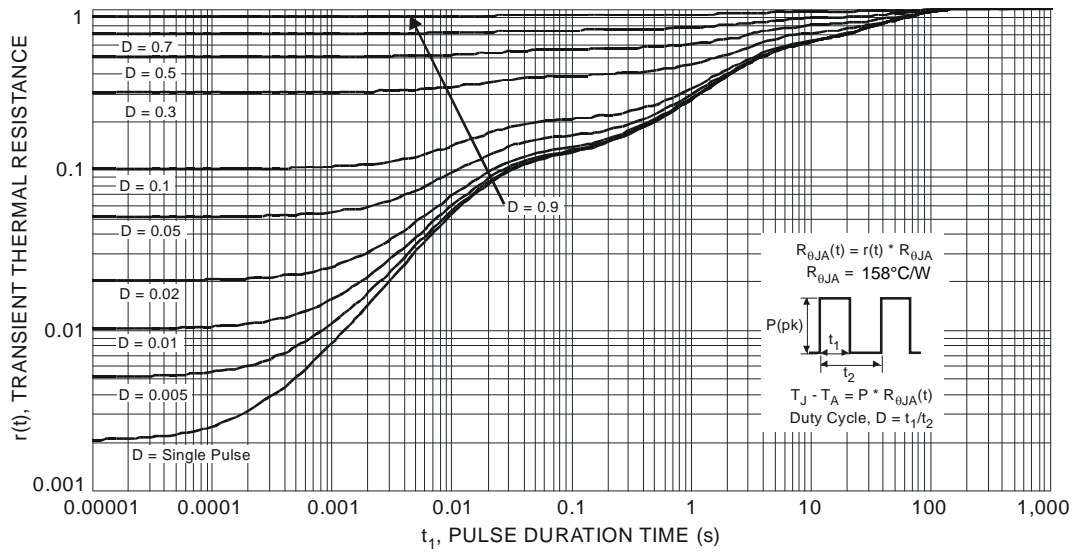
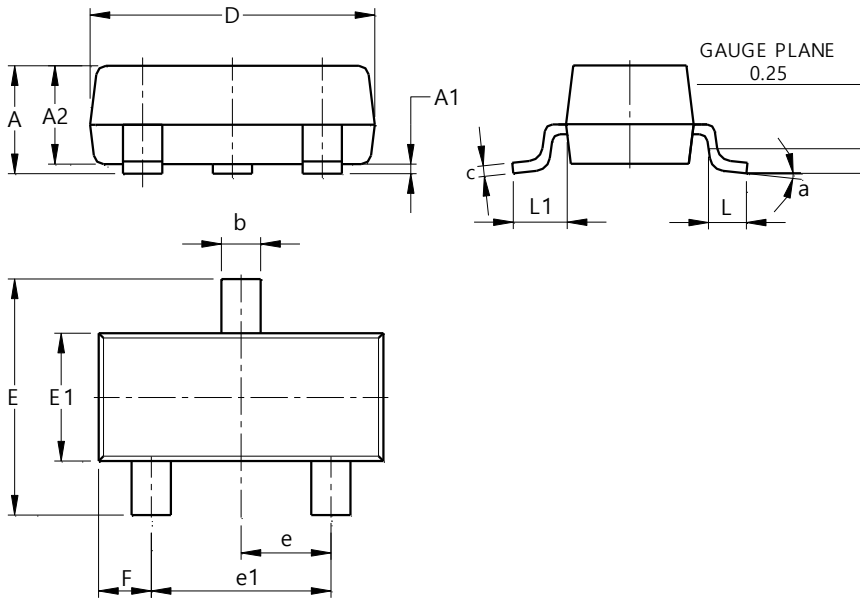


Fig. 14 Transient Thermal Response

**Package Outline Dimensions**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT23 (Standard)**

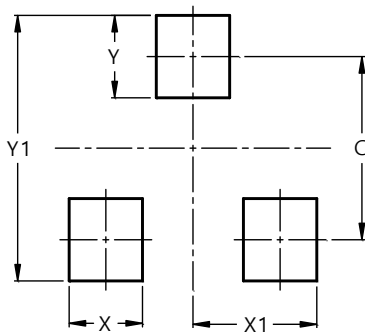


SOT23 (Standard)			
Dim	Min	Max	Typ
A	0.90	1.15	1.025
A1	0.00	0.10	0.05
A2	0.85	1.10	0.975
b	0.30	0.51	0.40
c	0.080	0.202	0.11
D	2.80	3.00	2.90
E	2.25	2.55	2.40
E1	1.20	1.40	1.30
e	0.89	1.03	0.915
e1	1.78	2.05	1.83
F	0.40	0.60	0.535
L1	0.45	0.61	0.55
L	0.25	0.55	0.40
a	0°	8°	--
All Dimensions in mm			

**Suggested Pad Layout**

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

**SOT23 (Standard)**



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9

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